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4. the top figure depicts the growth of a si/aln bilayer and the interface between a gan layer grown on the si/aln bilayer and a psi/sio2 bilayer. (a) shows the atomic force microscope (afm) image of a psi/sio2 bilayer. the gan layer was grown over a si/aln layer. (b) shows an atomic force microscope (afm) image of a si/aln bilayer. the si/aln layer was grown over a psi/sio2 bilayer. (c) shows the focused ion beam (fib) milled trench for the bilayer sample. the dark regions represent the psi/sio2 bilayer and the white regions represent the si/aln bilayer. (d) shows the cross-sectional scanning electron microscopy (sem) image of the bilayer sample. the dark region represents a psi/sio2 bilayer, the si/aln bilayer has been removed by the fib milling process, and the white region represents a gan layer. 5. silicon (si) is usually doped in both n- and p-type to fabricate si-doped anisotropic growth gan (sga-gan). the si is doped in the p-type on the {1014} side facet and in the n-type on the {0121} side facet, to break the symmetry and cause selective growth on the {1014} side. the threading dislocation density of sga-gan is typically much lower than that of n-gan/p-gan junction-type gan, but the density of threading dislocations is close to that of n-type gan/p-type gan junction-type gan. usually, to realize the high-performance device, epitaxial lateral overgrowth (elog) and selective area growth (sag) are used in order to reduce the threading dislocation density and reduce the two-dimensional hole accumulation layer. however, there is no report in previous studies about the effect of selective growth rate to reduce the threading dislocation density.

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we report a study of the influence of the initial surface orientation of the gan(001) surface on dislocation pile-ups and their activation during annealing. from the annealing of a 20x50 mm² gan(001) substrate at temperatures ranging from 800 to 1200^oc for 20min, we have found that, although the dislocation pile-ups are formed in all cases, the number of the dislocations increases with annealing temperature. the dislocation density on the gan(001) surface increases from $\sim 10^8$ cm⁻² for annealing at 800^oc to $\sim 10^9$ cm⁻² for annealing at 1200^oc, with only one polarity of edge dislocations observed. to understand the influence of the initial surface orientation of the gan(001) surface on the dislocations, the dislocations were counted using the principles of the dislocation density calculation method and the dislocation pile-ups were examined using high-resolution transmission electron microscopy (tem). we found that the initial surface orientation of the gan(001) has a strong influence on the type and density of dislocations and on the dislocation pile-ups. most importantly, we have found that, if the surface orientation of the gan(001) is aligned along the [111] direction, the dislocations can be effectively activated during annealing. this is because the high-energy dislocations propagate along this direction, and the dislocations pile up to form the dislocation pile-ups due to the anisotropic properties of this orientation. on the other hand, if the surface orientation of the gan(001) is along the [0001] direction, there are only few dislocations, and the pile-ups do not appear during annealing. the findings of this work will be helpful for the fabrication of gan optoelectronic devices, and the design of gan surface orientations for different applications. 5ec8ef588b

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